

**Features :**

- n Isolated mounting base 2500V~
- n Pressure contact technology with Increased power cycling capability
- n Space and weight saving

**Typical Applications :**

- n Inverter
- n Inductive heating
- n Chopper

V <sub>RRM</sub> , V <sub>DRM</sub>	Type & Outline	
600V	MKx200-06-413F3D	MHx200-06-413F3D
800V	MKx200-08-413F3D	MHx200-08-413F3D
1000V	MKx200-10-413F3D	MHx200-10-413F3D
1200V	MKx200-12-413F3D	MHx200-12-413F3D
1400V	MKx200-14-413F3D	MHx200-14-413F3D
1600V	MKx200-16-413F3D	MHx200-16-413F3D
1800V	MKx200-18-413F3D	MHx200-18-413F3D
1800V	MK200-18-413F3DG	

MKx stands for any type of **MKC, MKA, MKK**  
 MHx stands for any type of **MHC, MHA, MHK**

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T <sub>j</sub> (°C)	VALUE			UNIT	
				Min	Type	Max		
I <sub>T(AV)</sub>	Mean on-state current	180° half sine wave 50Hz Single side cooled, T <sub>c</sub> =85°C	125			200	A	
I <sub>T(RMS)</sub>	RMS on-state current					314	A	
I <sub>DRM</sub> I <sub>RRM</sub>	Repetitive peak current	at V <sub>DRM</sub> at V <sub>RRM</sub>	125			50	mA	
I <sub>TSM</sub>	Surge on-state current	10ms half sine wave	125			4.8	kA	
I <sup>2</sup> t	I <sup>2</sup> t for fusing coordination	V <sub>R</sub> =60%V <sub>RRM</sub>				115	10 <sup>3</sup> A <sup>2</sup> s	
V <sub>TO</sub>	Threshold voltage		125			1.65	V	
r <sub>T</sub>	On-state slope resistance					0.60	m	
V <sub>TM</sub>	Peak on-state voltage	I <sub>TM</sub> =600A	25			2.65	V	
dv/dt	Critical rate of rise of off-state voltage	V <sub>DM</sub> =67%V <sub>DRM</sub>	125			800	V/μs	
di/dt	Critical rate of rise of on-state current	Gate source 1.5A t <sub>r</sub> ≤0.5μs Repetitive	125			200	A/μs	
t <sub>q</sub>	Circuit commutated turn-off time	I <sub>TM</sub> =200A, t <sub>p</sub> =4000μs, V <sub>R</sub> =100V dv/dt=30V/μs, di/dt=-20A/μs	125	20		40	μs	
			25	6		16	μs	
I <sub>GT</sub>	Gate trigger current	V <sub>A</sub> =12V, I <sub>A</sub> =1A	25			30	mA	
V <sub>GT</sub>	Gate trigger voltage					0.8	2.5	V
I <sub>H</sub>	Holding current					20	200	mA
I <sub>L</sub>	Latching current						1000	mA
V <sub>GD</sub>	Non-trigger gate voltage	V <sub>DM</sub> =67%V <sub>DRM</sub>	125			0.2	V	
R <sub>th(j-c)</sub>	Thermal resistance Junction to case	Single side cooled per chip				0.100	°C /W	
R <sub>th(c-h)</sub>	Thermal resistance case to heatsink	Single side cooled per chip				0.040	°C /W	
V <sub>iso</sub>	Isolation voltage	50Hz, R.M.S, t=1min, I <sub>iso</sub> : 1mA(MAX)		2500			V	
F <sub>m</sub>	Terminal connection torque(M8)			10.0		12.0	N·m	
	Mounting torque(M6)			4.5		6.0	N·m	
T <sub>vj</sub>	Junction temperature			-40		125	°C	
T <sub>stg</sub>	Stored temperature			-40		125	°C	
W <sub>t</sub>	Weight				770		g	
Outline	413F3D							

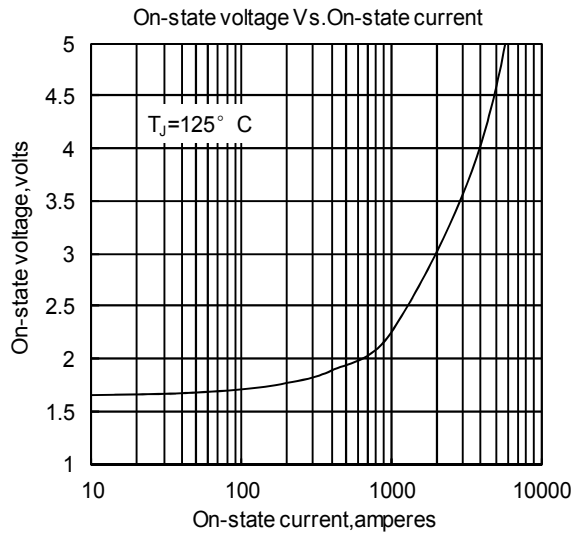


Fig.1

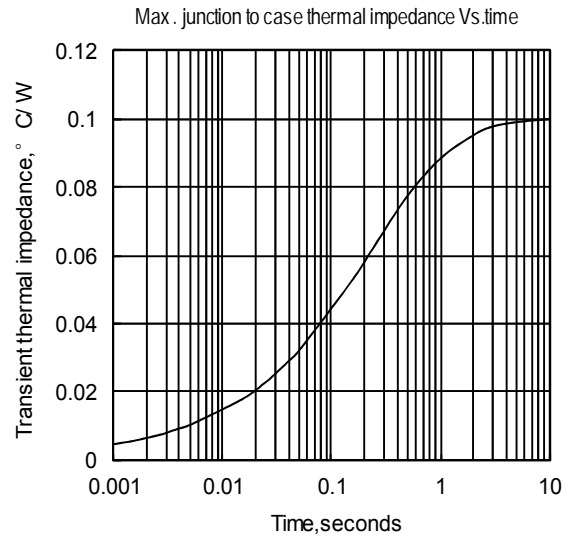


Fig.2

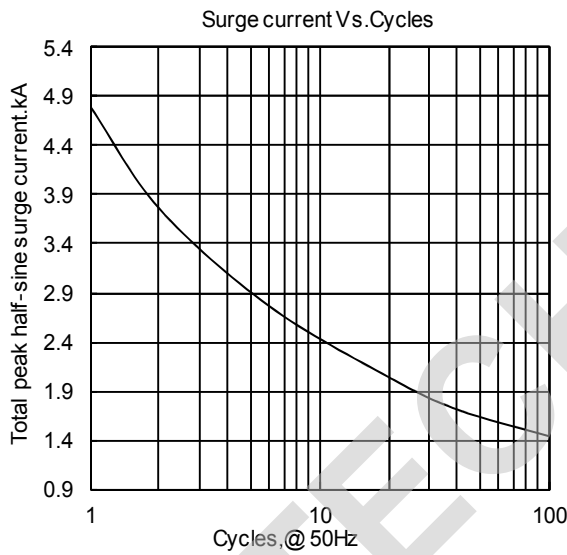


Fig.3

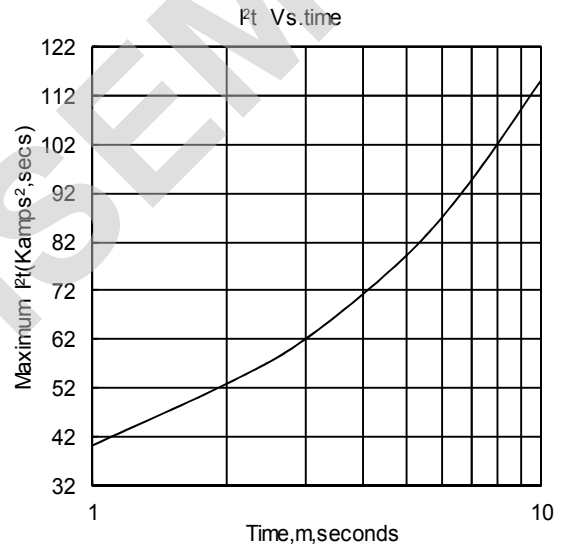


Fig.4

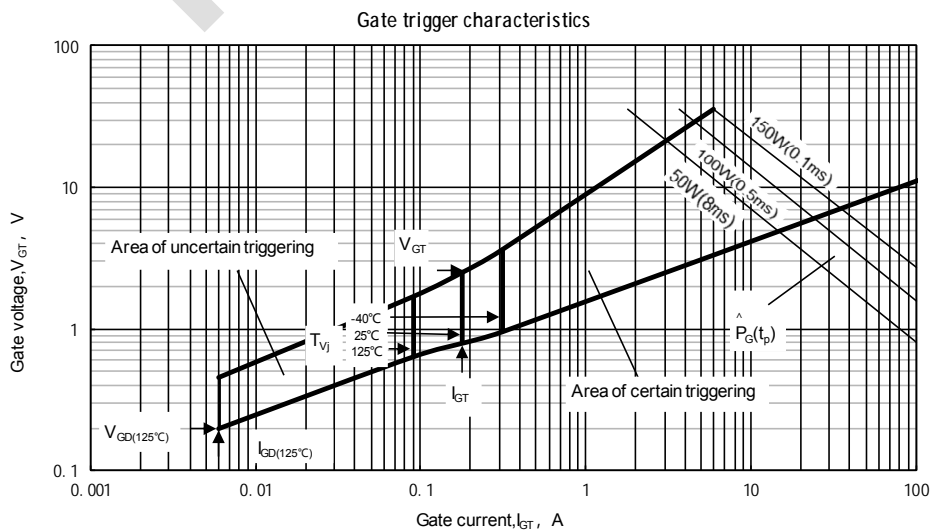
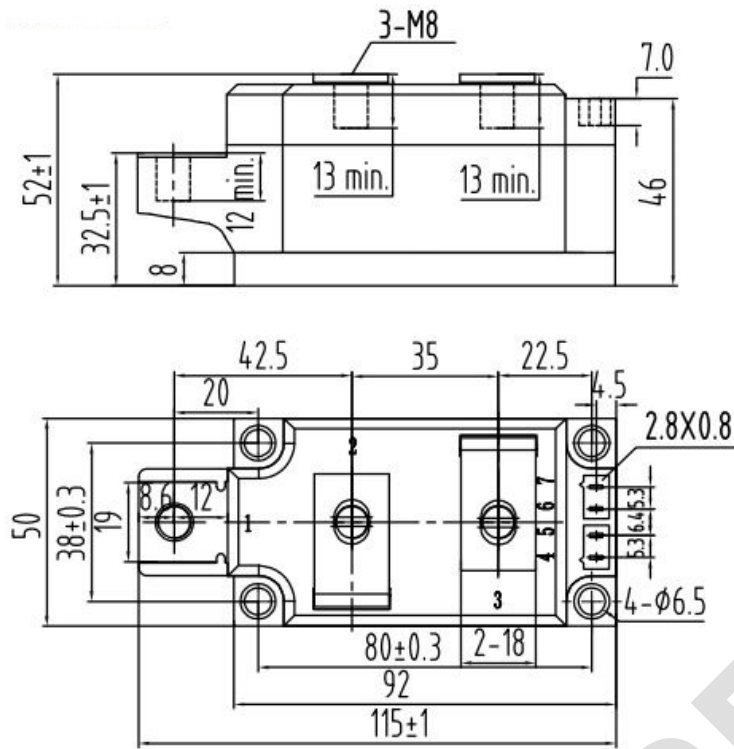


Fig.5

Outline:



Unmarked dimensional tolerance: ±0.5mm

TECHSEM reserves the right to change specifications without notice.

